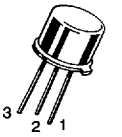
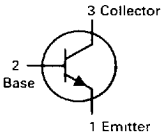
Boca Semiconductor Corp.

2N3019★
2N3020

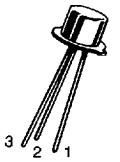
CASE 79-04, STYLE 1
TO-39 (TO-205AD)





2N3700★

CASE 22-03, STYLE 1
TO-18 (TO-206AA)



GENERAL TRANSISTORS

NPN SILICON

★2N3019 and 2N3700 are Motorola designated preferred devices.

MAXIMUM RATINGS

Rating	Symbol	2N3019 2N3020	2N3700	Unit
Collector-Emitter Voltage	V_{CEO}	80	80	Vdc
Collector-Base Voltage	V_{CBO}	140	140	Vdc
Emitter-Base Voltage	V_{EBO}	7.0	7.0	Vdc
Collector Current — Continuous	I_C	1.0	1.0	Adc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	0.8 4.6	0.5 2.85	Watts mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	5.0 28.6	1.8 10.6	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	2N3019 2N3020	2N3700	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	217	350	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	35	97	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

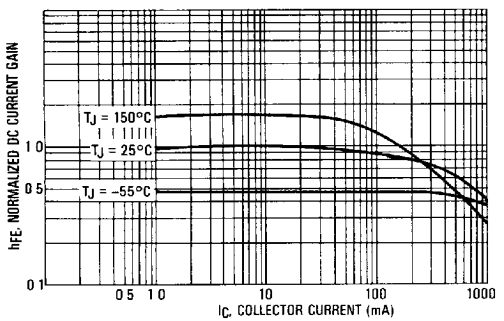
Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I_C = 30 mAdc, I_B = 0)		$V_{(BR)CEO}$	80	—	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)		$V_{(BR)CBO}$	140	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)		$V_{(BR)EBO}$	7.0	—	Vdc
Collector Cutoff Current (V_{CB} = 90 Vdc, I_E = 0) (V_{CB} = 90 Vdc, I_E = 0, T_A = +150°C)		I_{CBO}	— —	0.01 10	μAdc
Emitter Cutoff Current (V_{EB} = 5.0 Vdc, I_C = 0)		I_{EBO}	—	0.010	μAdc
ON CHARACTERISTICS					
DC Current Gain		h_{FE}			—
(I_C = 0.1 mAdc, V_{CE} = 10 Vdc)	2N3700, 2N3019		50	—	
	2N3020		30	100	
(I_C = 10 mAdc, V_{CE} = 10 Vdc)(1)	2N3700, 2N3019		90	—	
	2N3020		40	120	
(I_C = 150 mAdc, V_{CE} = 10 Vdc)(1)	2N3700, 2N3019		100	300	
	2N3020		40	120	
(I_C = 150 mAdc, V_{CE} = 10 Vdc, T_C = −55°C)(1)	2N3700, 2N3019		40	—	
(I_C = 500 mAdc, V_{CE} = 10 Vdc)(1)	2N3700, 2N3019		50	—	
	2N3020		30	100	
(I_C = 1.0 Adc, V_{CE} = 10 Vdc)(1)	All Types		15	—	
Collector-Emitter Saturation Voltage(1) (I_C = 150 mAdc, I_B = 15 mAdc) (I_C = 500 mAdc, I_B = 50 mAdc)		$V_{CE(sat)}$	— —	0.2 0.5	Vdc
Base-Emitter Saturation Voltage(1) (I_C = 150 mAdc, I_B = 15 mAdc)		$V_{BE(sat)}$	—	1.1	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I_C = 50 mAdc, V_{CE} = 10 Vdc, f = 20 MHz)	2N3020 2N3019, 2N3700	f_T	80 100	— 400	MHz

ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

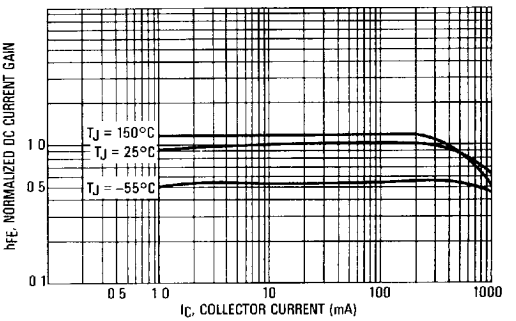
Characteristic		Symbol	Min	Max	Unit
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)		C_{obo}	—	12	pF
Input Capacitance (V_{EB} = 0.5 Vdc, I_C = 0, f = 1.0 MHz		C_{ibo}	—	60	pF
Small-Signal Current Gain (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)	2N3700, 2N3019 2N3020	h_{fe}	 80 30	 400 200	—
Collector Base Time Constant (I_E = 10 mAdc, V_{CB} = 10 Vdc, f = 79.8 MHz)	2N3019, 2N3020 2N3700	$rb'C_c$	 — 15	 400 400	ps
Noise Figure (I_C = 100 μAdc, V_{CE} = 10 Vdc, R_S = 1.0 k ohms, f = 1.0 kHz)	2N3019, 2N3700	NF	—	4	dB

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 1.0%.

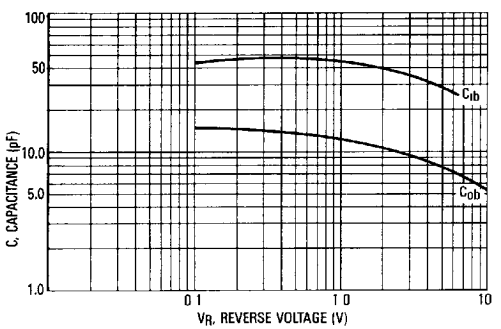
DC CURRENT GAIN
2N3019, 2N3700



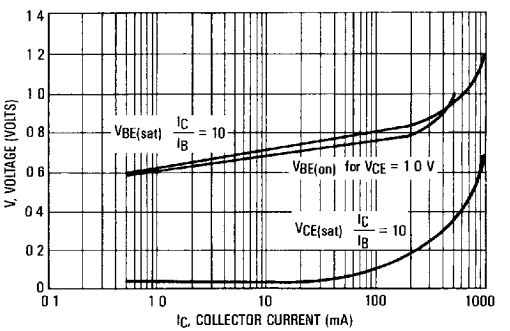
DC CURRENT GAIN
2N3020



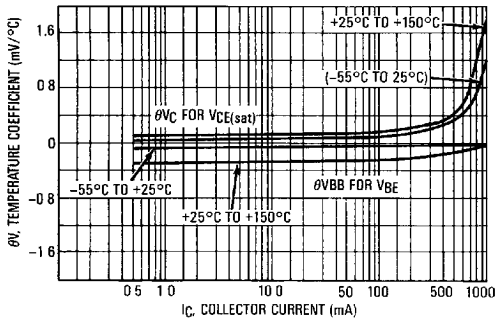
CAPACITANCE



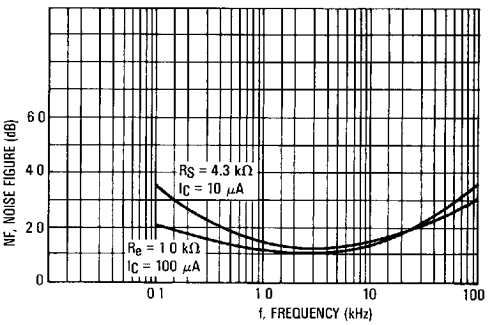
"ON" VOLTAGES



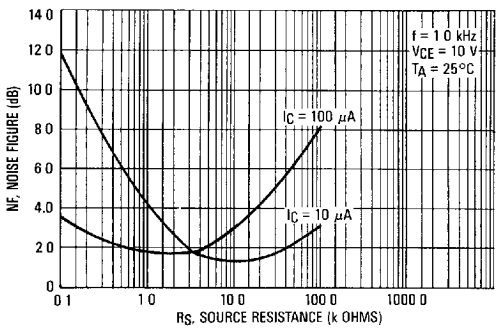
TEMPERATURE COEFFICIENTS



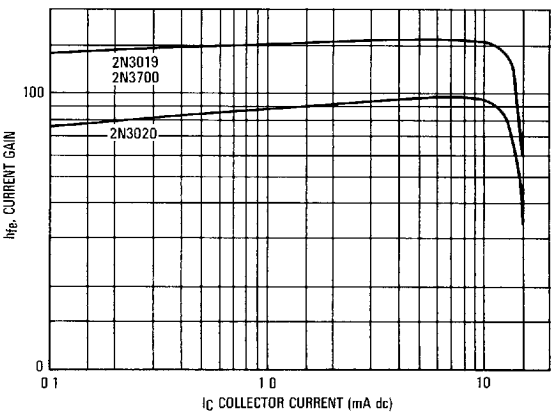
FREQUENCY EFFECTS



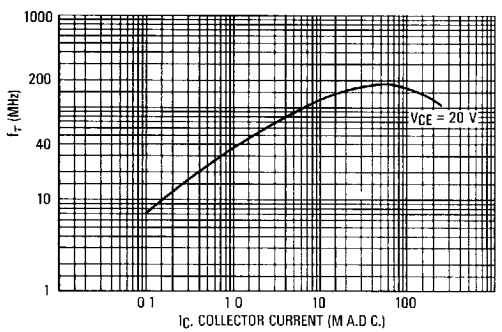
SOURCE RESISTANCE EFFECTS



CURRENT GAIN BANDWIDTH PRODUCT versus COLLECTOR CURRENT — 1 kHz h_{fe}



CURRENT GAIN — BANDWIDTH PRODUCT



ACTIVE REGION SAFE OPERATING AREA